

# FNA41560 / FNA41560B2

## Motion SPM® 45 Series

### Features

- UL Certified No. E209204 (UL1557)
- 600 V - 15 A 3-Phase IGBT Inverter with Integral Gate Drivers and Protection
- Low Thermal Resistance Using Ceramic Substrate
- Low-Loss, Short-Circuit Rated IGBTs
- Built-In Bootstrap Diodes and Dedicated Vs Pins Simplify PCB Layout
- Built-In NTC Thermistor for Temperature Monitoring
- Separate Open-Emitter Pins from Low-Side IGBTs for Three-Phase Current Sensing
- Single-Grounded Power Supply
- Optimized for 5 kHz Switching Frequency
- Isolation Rating: 2000 V<sub>rms</sub> / min.

### Applications

- Motion Control - Home Appliance / Industrial Motor

### Related Resources

- [AN-9070 - Motion SPM® 45 Series Users Guide](#)
- [AN-9071 - Motion SPM® 45 Series Thermal Performance Information](#)
- [AN-9072 - Motion SPM® 45 Series Mounting Guidance](#)
- [RD-344 - Reference Design \(Three Shunt Solution\)](#)
- [RD-345 - Reference Design \(One Shunt Solution\)](#)

### General Description

FNA41560 / FNA41560B2 is a Motion SPM® 45 module providing a fully-featured, high-performance inverter output stage for AC Induction, BLDC, and PMSM motors. These modules integrate optimized gate drive of the built-in IGBTs to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockouts, over-current shutdown, thermal monitoring, and fault reporting. The built-in, high-speed HVIC requires only a single supply voltage and translates the incoming logic-level gate inputs to the high-voltage, high-current drive signals required to properly drive the module's robust short-circuit-rated IGBTs. Separate negative IGBT terminals are available for each phase to support the widest variety of control algorithms.

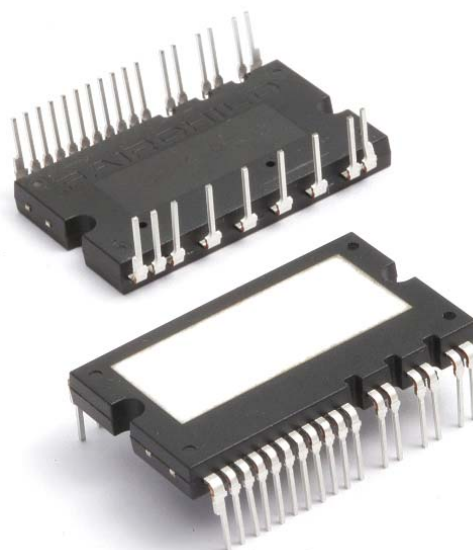


Figure 1. Package Overview

### Package Marking and Ordering Information

Device	Device Marking	Package	Packing Type	Quantity
FNA41560	FNA41560	SPMAA-A26	Rail	12
FNA41560B2	FNA41560B2	SPMAA-C26	Rail	12

## Integrated Power Functions

- 600 V - 15 A IGBT inverter for three-phase DC / AC power conversion (please refer to Figure 3)

## Integrated Drive, Protection, and System Control Functions

- For inverter high-side IGBTs: gate drive circuit, high-voltage isolated high-speed level shifting control circuit Under-Voltage Lock-Out (UVLO) protection
- For inverter low-side IGBTs: gate drive circuit, Short-Circuit Protection (SCP) control supply circuit Under-Voltage Lock-Out (UVLO) protection
- Fault signaling: corresponding to UVLO (low-side supply) and SC faults
- Input interface: active-HIGH interface, works with 3.3 / 5 V logic, Schmitt trigger input

## Pin Configuration

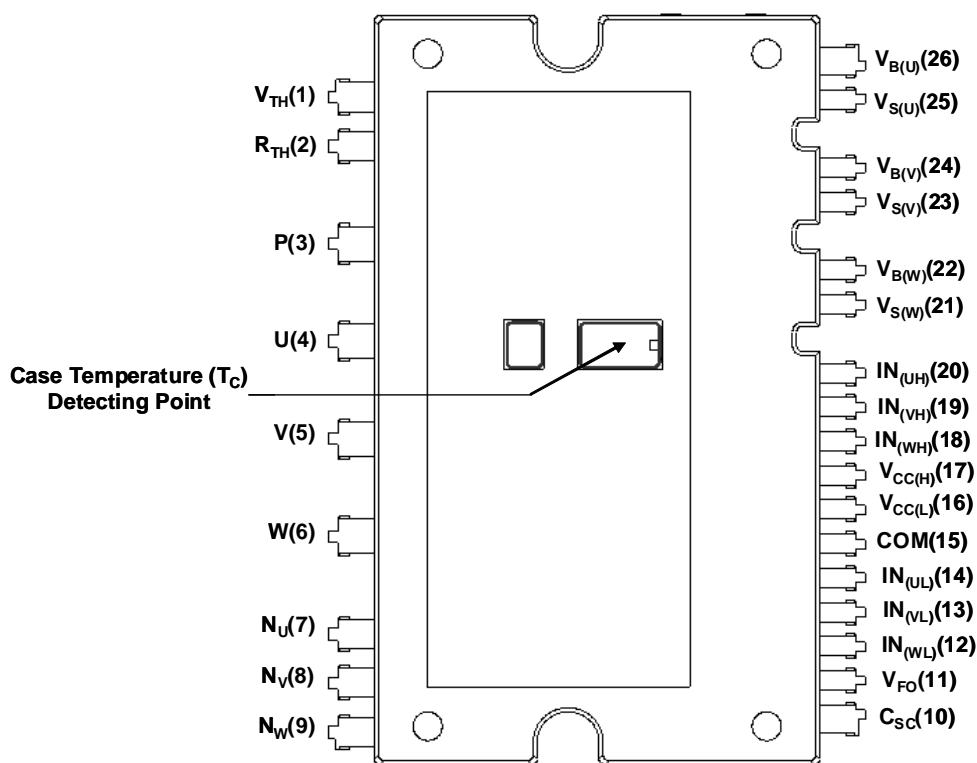
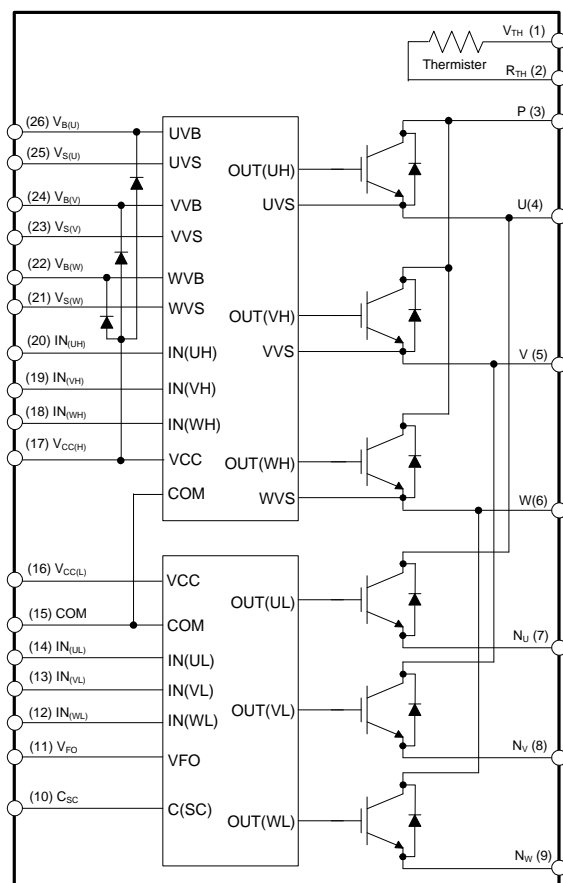


Figure 2. Top View

## Pin Descriptions

Pin Number	Pin Name	Pin Description
1	$V_{TH}$	Thermistor Bias Voltage
2	$R_{TH}$	Series Resistor for the Use of Thermistor (Temperature Detection)
3	P	Positive DC-Link Input
4	U	Output for U-Phase
5	V	Output for V-Phase
6	W	Output for W-Phase
7	$N_U$	Negative DC-Link Input for U-Phase
8	$N_V$	Negative DC-Link Input for V-Phase
9	$N_W$	Negative DC-Link Input for W-Phase
10	$C_{SC}$	Capacitor (Low-Pass Filter) for Short-circuit Current Detection Input
11	$V_{FO}$	Fault Output
12	$IN_{(WL)}$	Signal Input for Low-Side W-Phase
13	$IN_{(VL)}$	Signal Input for Low-Side V-Phase
14	$IN_{(UL)}$	Signal Input for Low-Side U-Phase
15	COM	Common Supply Ground
16	$V_{CC(L)}$	Low-Side Common Bias Voltage for IC and IGBTs Driving
17	$V_{CC(H)}$	High-Side Common Bias Voltage for IC and IGBTs Driving
18	$IN_{(WH)}$	Signal Input for High-Side W-Phase
19	$IN_{(VH)}$	Signal Input for High-Side V-Phase
20	$IN_{(UH)}$	Signal Input for High-Side U-Phase
21	$V_{S(W)}$	High-Side Bias Voltage Ground for W-Phase IGBT Driving
22	$V_{B(W)}$	High-Side Bias Voltage for W-Phase IGBT Driving
23	$V_{S(V)}$	High-Side Bias Voltage Ground for V-Phase IGBT Driving
24	$V_{B(V)}$	High-Side Bias Voltage for V-Phase IGBT Driving
25	$V_{S(U)}$	High-Side Bias Voltage Ground for U-Phase IGBT Driving
26	$V_{B(U)}$	High-Side Bias Voltage for U-Phase IGBT Driving

## Internal Equivalent Circuit and Input/Output Pins



**Figure 3. Internal Block Diagram**

**1st Notes:**

1. Inverter high-side is composed of three IGBTs, freewheeling diodes, and one control IC for each IGBT.
2. Inverter low-side is composed of three IGBTs, freewheeling diodes, and one control IC for each IGBT. It has gate drive and protection functions.
3. Inverter power side is composed of four inverter DC-link input terminals and three inverter output terminals.

**Absolute Maximum Ratings** ( $T_J = 25^\circ\text{C}$ , unless otherwise specified.)**Inverter Part**

Symbol	Parameter	Conditions	Rating	Unit
$V_{PN}$	Supply Voltage	Applied between P - $N_U$ , $N_V$ , $N_W$	450	V
$V_{PN(\text{Surge})}$	Supply Voltage (Surge)	Applied between P - $N_U$ , $N_V$ , $N_W$	500	V
$V_{CES}$	Collector - Emitter Voltage		600	V
$\pm I_C$	Each IGBT Collector Current	$T_C = 25^\circ\text{C}$ , $T_J < 150^\circ\text{C}$	15	A
$\pm I_{CP}$	Each IGBT Collector Current (Peak)	$T_C = 25^\circ\text{C}$ , $T_J < 150^\circ\text{C}$ , Under 1 ms Pulse Width	30	A
$P_C$	Collector Dissipation	$T_C = 25^\circ\text{C}$ per Chip	41	W
$T_J$	Operating Junction Temperature	(2nd Note 1)	- 40 ~ 150	$^\circ\text{C}$

**2nd Notes:**

1. The maximum junction temperature rating of the power chips integrated within the Motion SPM® 45 product is  $150^\circ\text{C}$ .

**Control Part**

Symbol	Parameter	Conditions	Rating	Unit
$V_{CC}$	Control Supply Voltage	Applied between $V_{CC(H)}$ , $V_{CC(L)}$ - COM	20	V
$V_{BS}$	High - Side Control Bias Voltage	Applied between $V_{B(U)}$ - $V_{S(U)}$ , $V_{B(V)}$ - $V_{S(V)}$ , $V_{B(W)}$ - $V_{S(W)}$	20	V
$V_{IN}$	Input Signal Voltage	Applied between $IN_{(UH)}$ , $IN_{(VH)}$ , $IN_{(WH)}$ , $IN_{(UL)}$ , $IN_{(VL)}$ , $IN_{(WL)}$ - COM	-0.3 ~ $V_{CC} + 0.3$	V
$V_{FO}$	Fault Output Supply Voltage	Applied between $V_{FO}$ - COM	-0.3 ~ $V_{CC} + 0.3$	V
$I_{FO}$	Fault Output Current	Sink Current at $V_{FO}$ pin	1	mA
$V_{SC}$	Current-Sensing Input Voltage	Applied between $C_{SC}$ - COM	-0.3 ~ $V_{CC} + 0.3$	V

**Bootstrap Diode Part**

Symbol	Parameter	Conditions	Rating	Unit
$V_{RRM}$	Maximum Repetitive Reverse Voltage		600	V
$I_F$	Forward Current	$T_C = 25^\circ\text{C}$ , $T_J < 150^\circ\text{C}$	0.50	A
$I_{FP}$	Forward Current (Peak)	$T_C = 25^\circ\text{C}$ , $T_J < 150^\circ\text{C}$ , Under 1 ms Pulse Width	1.50	A
$T_J$	Operating Junction Temperature		-40 ~ 150	$^\circ\text{C}$

**Total System**

Symbol	Parameter	Conditions	Rating	Unit
$V_{PN(\text{PROT})}$	Self-Protection Supply Voltage Limit (Short-Circuit Protection Capability)	$V_{CC} = V_{BS} = 13.5 \sim 16.5 \text{ V}$ $T_J = 150^\circ\text{C}$ , Non-Repetitive, $< 2 \mu\text{s}$	400	V
$T_{STG}$	Storage Temperature		-40 ~ 125	$^\circ\text{C}$
$V_{ISO}$	Isolation Voltage	60 Hz, Sinusoidal, AC 1 Minute, Connect Pins to Heat Sink Plate	2000	$V_{rms}$

**Thermal Resistance**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$R_{th(j-c)Q}$	Junction to Case Thermal Resistance	Inverter IGBT Part (per 1 / 6 module)	-	-	3.0	$^\circ\text{C} / \text{W}$
$R_{th(j-c)F}$		Inverter FWDi Part (per 1 / 6 module)	-	-	4.3	$^\circ\text{C} / \text{W}$

**2nd Notes:**

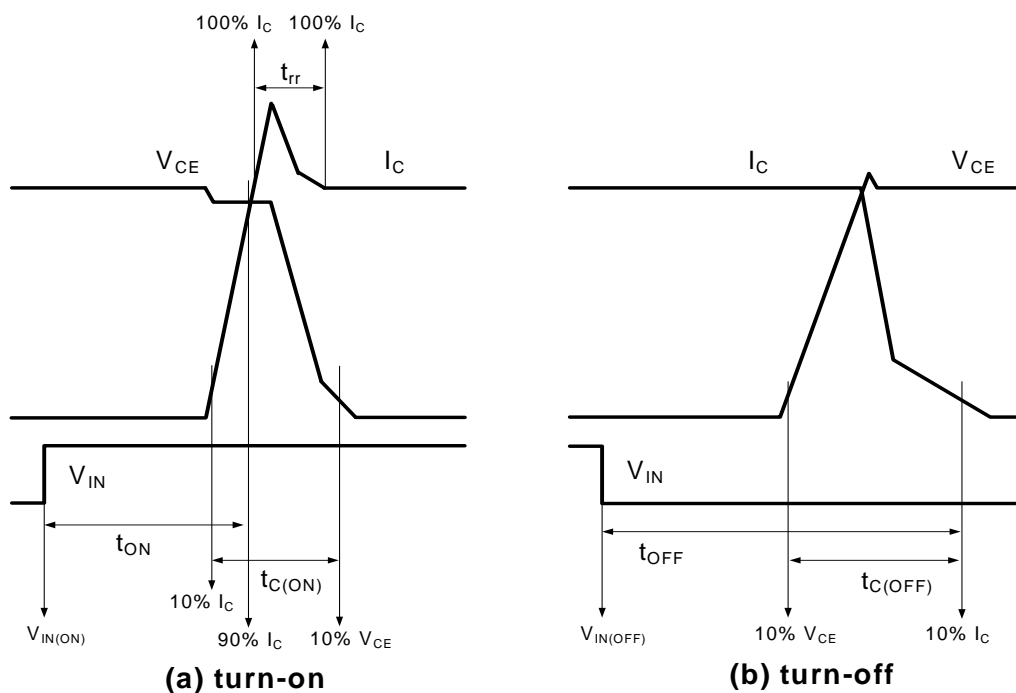
2. For the measurement point of case temperature ( $T_C$ ), please refer to Figure 2.

**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$ , unless otherwise specified.)**Inverter Part**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{CE(SAT)}$	Collector - Emitter Saturation Voltage	$V_{CC} = V_{BS} = 15\text{ V}$ $V_{IN} = 5\text{ V}$ $I_C = 15\text{ A}$ , $T_J = 25^\circ\text{C}$	-	1.8	2.3	V
$V_F$	FWDi Forward Voltage	$V_{IN} = 0\text{ V}$ $I_F = 15\text{ A}$ , $T_J = 25^\circ\text{C}$	-	1.8	2.3	V
HS	$t_{ON}$ $t_{C(ON)}$ $t_{OFF}$ $t_{C(OFF)}$ $t_{rr}$	Switching Times $V_{PN} = 300\text{ V}$ , $V_{CC} = V_{BS} = 15\text{ V}$ , $I_C = 15\text{ A}$ $T_J = 25^\circ\text{C}$ $V_{IN} = 0\text{ V} \leftrightarrow 5\text{ V}$ , Inductive Load (2nd Note 3)	0.45	0.75	1.25	$\mu\text{s}$
			-	0.25	0.50	$\mu\text{s}$
			-	0.75	1.25	$\mu\text{s}$
			-	0.25	0.50	$\mu\text{s}$
			-	0.15	-	$\mu\text{s}$
LS	$t_{ON}$ $t_{C(ON)}$ $t_{OFF}$ $t_{C(OFF)}$ $t_{rr}$	$V_{PN} = 300\text{ V}$ , $V_{CC} = V_{BS} = 15\text{ V}$ , $I_C = 15\text{ A}$ $T_J = 25^\circ\text{C}$ $V_{IN} = 0\text{ V} \leftrightarrow 5\text{ V}$ , Inductive Load (2nd Note 3)	0.45	0.75	1.25	$\mu\text{s}$
			-	0.25	0.50	$\mu\text{s}$
			-	0.75	1.25	$\mu\text{s}$
			-	0.25	0.50	$\mu\text{s}$
			-	0.15	-	$\mu\text{s}$
$I_{CES}$	Collector - Emitter Leakage Current	$V_{CE} = V_{CES}$	-	-	1	mA

**2nd Notes:**

3.  $t_{ON}$  and  $t_{OFF}$  include the propagation delay of the internal drive IC.  $t_{C(ON)}$  and  $t_{C(OFF)}$  are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.

**Figure 4. Switching Time Definition**

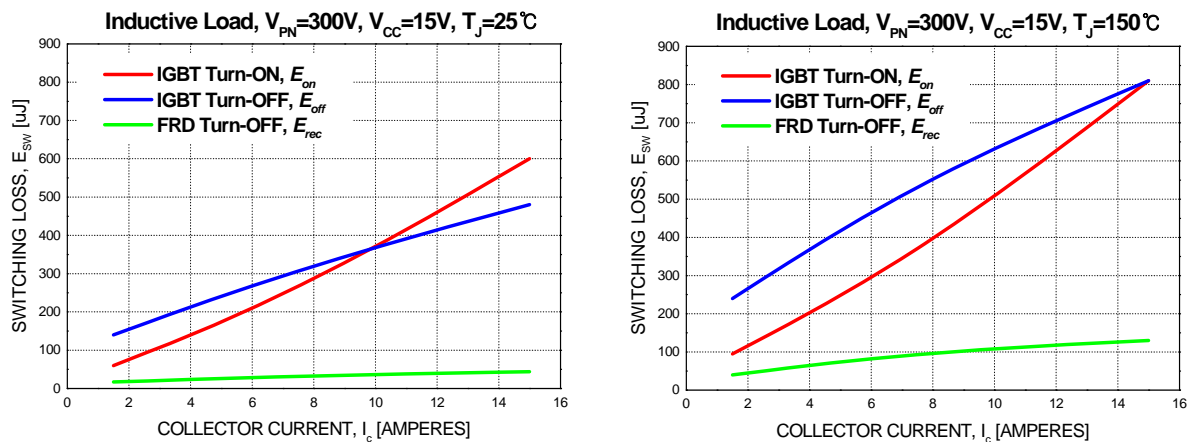


Figure 5. Switching Loss Characteristics (Typical)

## Control Part

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_{QCCH}$	Quiescent $V_{CC}$ Supply Current	$V_{CC(H)} = 15V$ , $I_{N(UH, VH, WH)} = 0V$	$V_{CC(H)} - COM$	-	-	0.10 mA
$I_{QCCL}$		$V_{CC(L)} = 15V$ , $I_{N(UL, VL, WL)} = 0V$	$V_{CC(L)} - COM$	-	-	2.65 mA
$I_{PCCH}$	Operating $V_{CC}$ Supply Current	$V_{CC(L)} = 15V$ , $f_{PWM} = 20kHz$ , duty = 50%, Applied to One PWM Signal Input for High-Side	$V_{CC(H)} - COM$	-	-	0.15 mA
$I_{PCCL}$		$V_{CC(L)} = 15V$ , $f_{PWM} = 20kHz$ , duty = 50%, Applied to One PWM Signal Input for Low-Side	$V_{CC(L)} - COM$	-	-	3.65 mA
$I_{QBS}$	Quiescent $V_{BS}$ Supply Current	$V_{BS} = 15V$ , $I_{N(UH, VH, WH)} = 0V$	$V_{B(U)} - V_{S(U)}$ , $V_{B(V)} - V_{S(V)}$ , $V_{B(W)} - V_{S(W)}$	-	-	0.30 mA
$I_{PBS}$	Operating $V_{BS}$ Supply Current	$V_{CC} = V_{BS} = 15V$ , $f_{PWM} = 20kHz$ , Duty = 50%, Applied to One PWM Signal Input for High-Side	$V_{B(U)} - V_{S(U)}$ , $V_{B(V)} - V_{S(V)}$ , $V_{B(W)} - V_{S(W)}$	-	-	2.00 mA
$V_{FOH}$	Fault Output Voltage	$V_{SC} = 0V$ , $V_{FO}$ Circuit: 10 k $\Omega$ to 5 V Pull-up	4.5	-	-	V
$V_{FOL}$		$V_{SC} = 1V$ , $V_{FO}$ Circuit: 10 k $\Omega$ to 5 V Pull-up	-	-	0.5	V
$V_{SC(ref)}$	Short-Circuit Current Trip Level	$V_{CC} = 15V$ (2nd Note 4)	0.45	0.50	0.55	V
$UV_{CCD}$	Supply Circuit Under-Voltage Protection	Detection level	10.5	-	13.0	V
$UV_{CCR}$		Reset level	11.0	-	13.5	V
$UV_{BSD}$		Detection level	10.0	-	12.5	V
$UV_{BSR}$		Reset level	10.5	-	13.0	V
$t_{FOD}$	Fault-Out Pulse Width		30	-	-	$\mu s$
$V_{IN(ON)}$	ON Threshold Voltage	Applied between $I_{N(UH)}$ , $I_{N(VH)}$ , $I_{N(WH)}$ , $I_{N(UL)}$ , $I_{N(VL)}$ , $I_{N(WL)} - COM$	-	-	2.6	V
$V_{IN(OFF)}$	OFF Threshold Voltage		0.8	-	-	V
$R_{TH}$	Resistance of Thermister	@ $T_{TH} = 25^\circ C$ , (2nd Note 5)	-	47	-	k $\Omega$
		@ $T_{TH} = 100^\circ C$	-	2.9	-	k $\Omega$

## 2nd Notes:

- Short-circuit protection is functioning only at the low-sides.
- $T_{TH}$  is the temperature of thermister itself. To know case temperature ( $T_C$ ), please make the experiment considering your application.

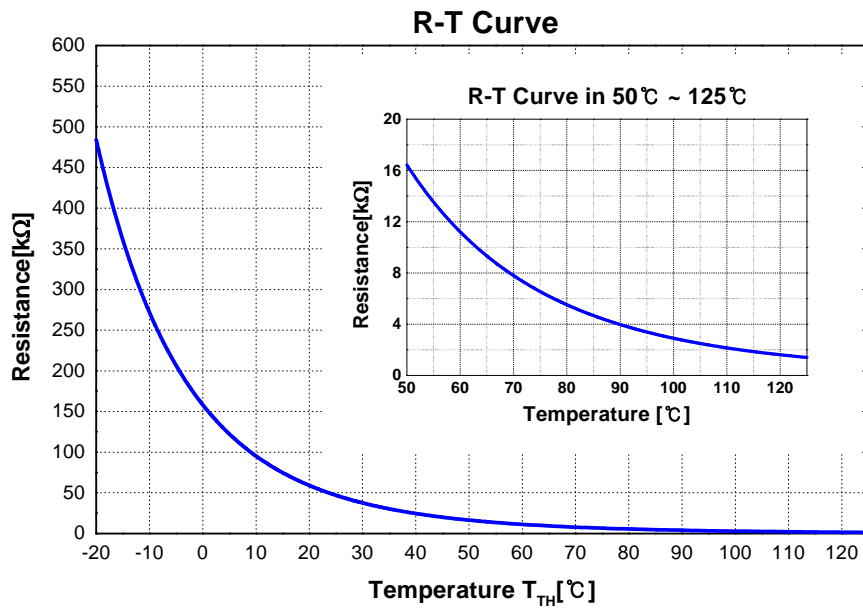


Figure. 6. R-T Curve of The Built-In Thermistor

#### Bootstrap Diode Part

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_F$	Forward Voltage	$I_F = 0.1 \text{ A}$ , $T_C = 25^\circ\text{C}$	-	2.5	-	V
$t_{rr}$	Reverse-Recovery Time	$I_F = 0.1 \text{ A}$ , $T_C = 25^\circ\text{C}$	-	80	-	ns

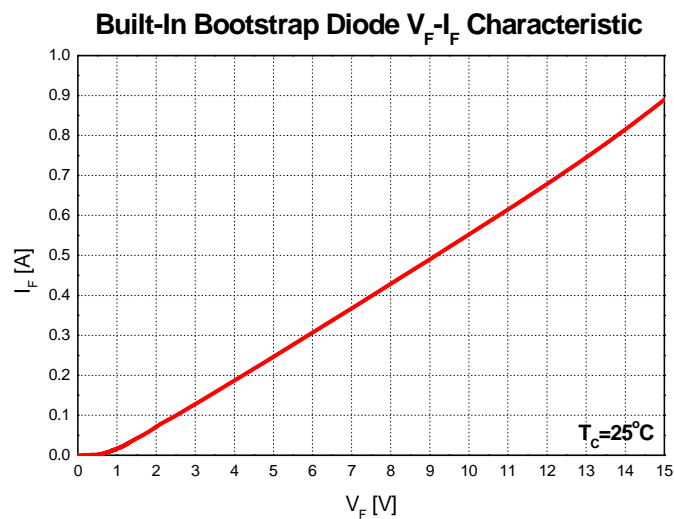


Figure 7. Built-In Bootstrap Diode Characteristic

#### 2nd Notes:

6. Built-in bootstrap diode includes around 15  $\Omega$  resistance characteristic.

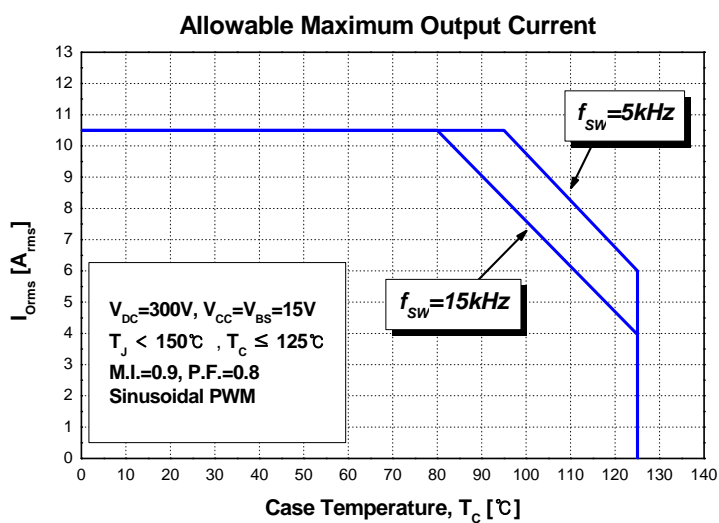


## Recommended Operating Conditions

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{PN}$	Supply Voltage	Applied between P - $N_U$ , $N_V$ , $N_W$	-	300	400	V
$V_{CC}$	Control Supply Voltage	Applied between $V_{CC(H)}$ , $V_{CC(L)}$ - COM	13.5	15.0	16.5	V
$V_{BS}$	High-Side Bias Voltage	Applied between $V_{B(U)}$ - $V_{S(U)}$ , $V_{B(V)}$ - $V_{S(V)}$ , $V_{B(W)}$ - $V_{S(W)}$	13.0	15.0	18.5	V
$dV_{CC}/dt$ , $dV_{BS}/dt$	Control Supply Variation		-1	-	1	V / $\mu$ s
$t_{dead}$	Blanking Time for Preventing Arm-Short	For each input signal	1.5	-	-	$\mu$ s
$f_{PWM}$	PWM Input Signal	$-40^{\circ}\text{C} < T_J < 150^{\circ}\text{C}$	-	-	20	kHz
$V_{SEN}$	Voltage for Current Sensing	Applied between $N_U$ , $N_V$ , $N_W$ - COM (Including Surge-Voltage)	-4		4	V
$P_{WIN(ON)}$	Minimum Input Pulse Width	(2nd Note 7)	0.5	-	-	$\mu$ s
$P_{WIN(OFF)}$			0.5	-	-	

### 2nd Notes:

7. This product might not make response if input pulse width is less than the recommended value.



**Figure 8. Allowable Maximum Output Current**

### 2nd Notes:

8. This allowable output current value is the reference data for the safe operation of this product. This may be different from the actual application and operating condition.

## Mechanical Characteristics and Ratings

Parameter	Conditions		Min.	Typ.	Max.	Unit
Device Flatness	See Figure 9		0	-	+ 120	μm
Mounting Torque	Mounting Screw: M3	Recommended 0.7 N • m	0.6	0.7	0.8	N • m
	See Figure 10	Recommended 7.1 kg • cm	6.2	7.1	8.1	kg • cm
Weight			-	11.00	-	g

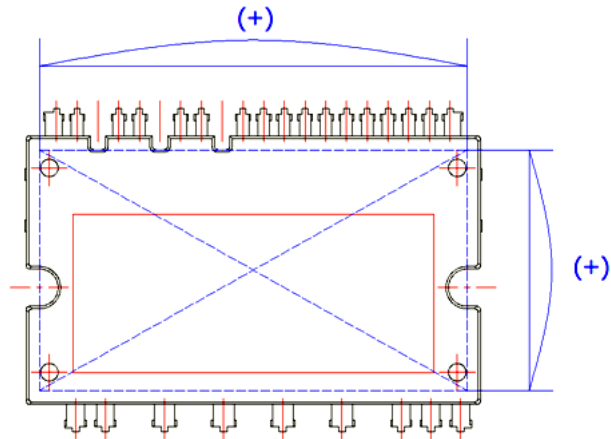


Figure 9. Flatness Measurement Position

**Pre - Screwing : 1→2**

**Final Screwing : 2→1**

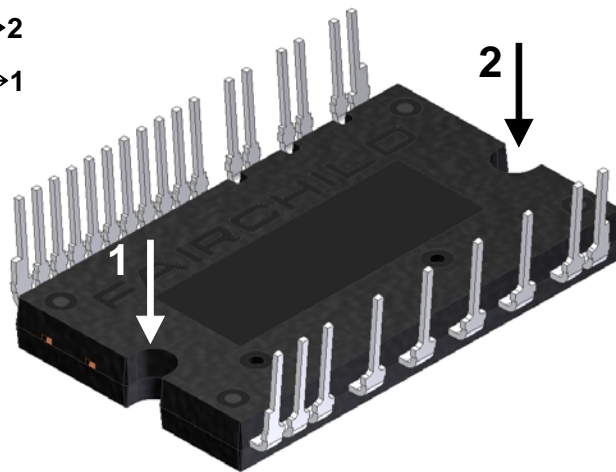
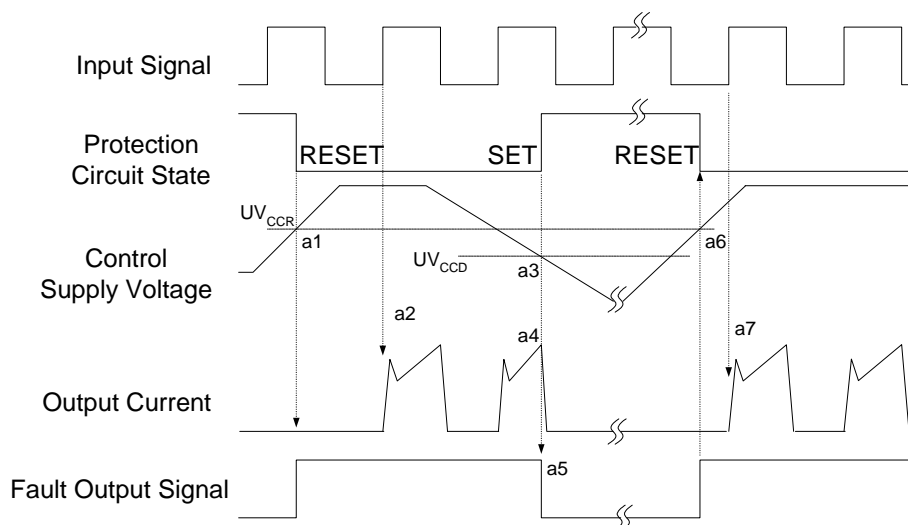


Figure 10. Mounting Screws Torque Order

### 2nd Notes:

9. Do not make over torque when mounting screws. Much mounting torque may cause ceramic cracks, as well as bolts and Al heat-sink destruction.
10. Avoid one side tightening stress. Figure 10 shows the recommended torque order for mounting screws. Uneven mounting can cause the ceramic substrate of the SPM® 45 package to be damaged. The pre-screwing torque is set to 20 ~ 30% of maximum torque rating.

## Time Charts of Protective Function



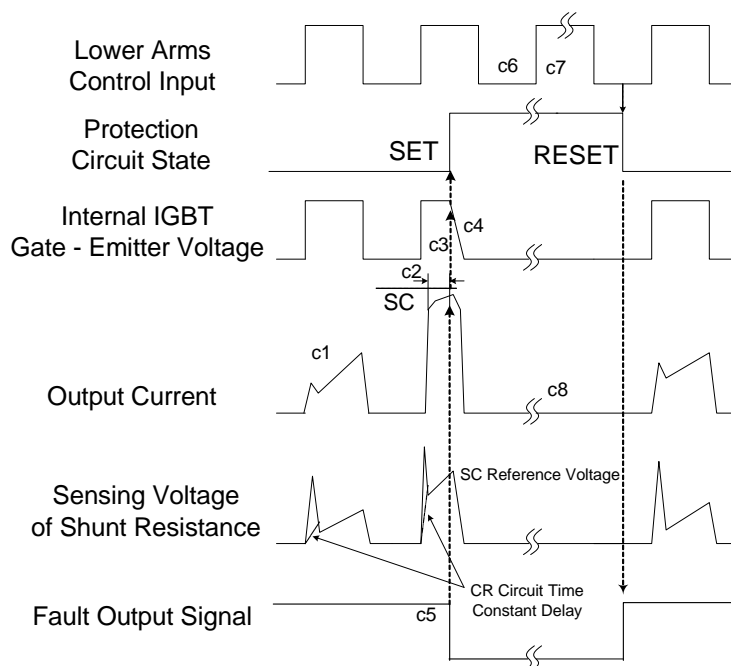
- a1 : Control supply voltage rises: after the voltage rises  $UV_{CCR}$ , the circuits start to operate when next input is applied.
- a2 : Normal operation: IGBT ON and carrying current.
- a3 : Under-voltage detection ( $UV_{CCD}$ ).
- a4 : IGBT OFF in spite of control input condition.
- a5 : Fault output operation starts.
- a6 : Under-voltage reset ( $UV_{CCR}$ ).
- a7 : Normal operation: IGBT ON and carrying current.

**Figure 11. Under-Voltage Protection (Low-Side)**



- b1 : Control supply voltage rises: after the voltage reaches  $UV_{BSR}$ , the circuits start to operate when next input is applied.
- b2 : Normal operation: IGBT ON and carrying current.
- b3 : Under-voltage detection ( $UV_{BSD}$ ).
- b4 : IGBT OFF in spite of control input condition, but there is no fault output signal.
- b5 : Under-voltage reset ( $UV_{BSR}$ ).
- b6 : Normal operation: IGBT ON and carrying current.

**Figure 12. Under-Voltage Protection (High-Side)**



(with the external shunt resistance and CR connection)

c1 : Normal operation: IGBT ON and carrying current.

c2 : Short-circuit current detection (SC trigger).

c3 : Hard IGBT gate interrupt.

c4 : IGBT turns OFF.

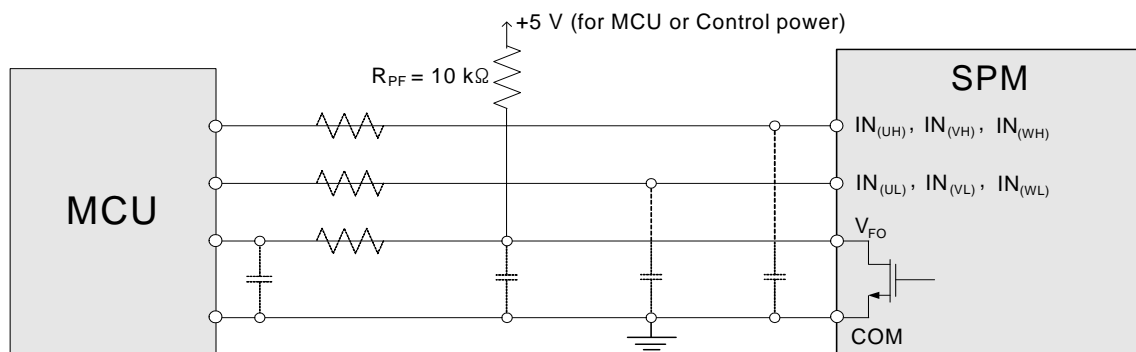
c5 : Input "LOW": IGBT OFF state.

c6 : Input "HIGH": IGBT ON state, but during the active period of fault output, the IGBT doesn't turn ON.

c7 : IGBT OFF state.

**Figure 13. Short-Circuit Protection (Low-Side Operation Only)**

## Input/Output Interface Circuit



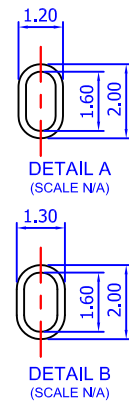
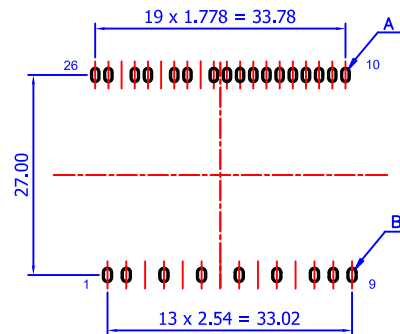
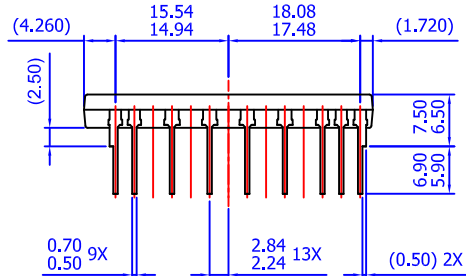
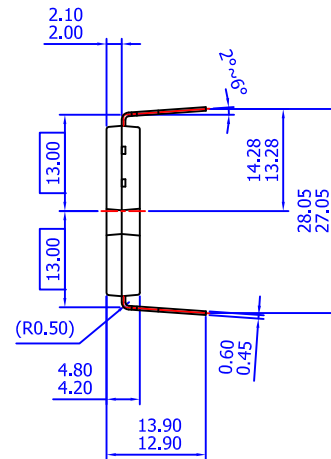
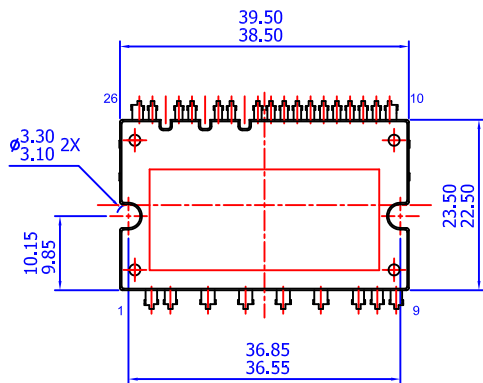
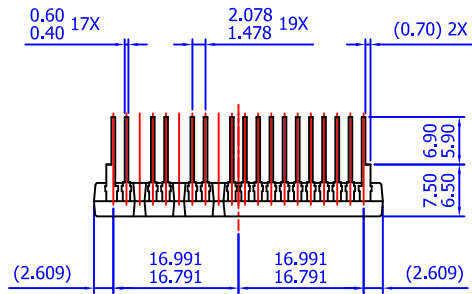
**Figure 14. Recommended MCU I/O Interface Circuit**

### 2nd Notes:

11. RC coupling at each input (parts shown dotted) might change depending on the PWM control scheme in the application and the wiring impedance of the application's printed circuit board. The input signal section of the Motion SPM® 45 product integrates a 5 kΩ (typ.) pull-down resistor. Therefore, when using an external filtering resistor, pay attention to the signal voltage drop at input terminal.

**3rd Notes:**

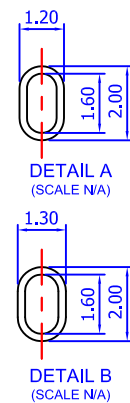
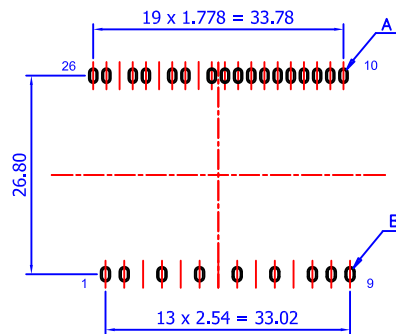
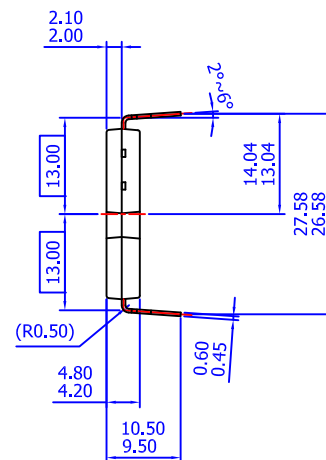
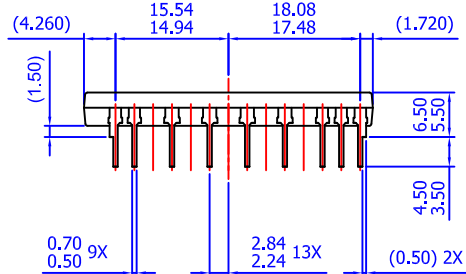
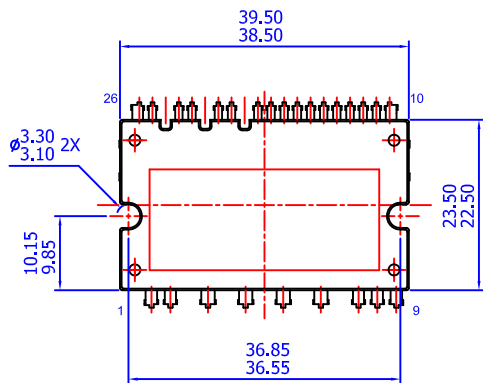
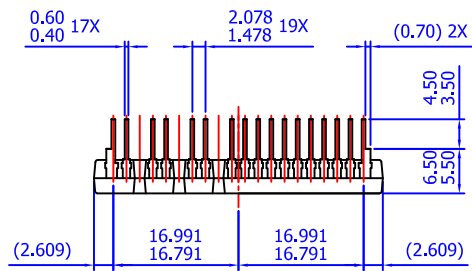
- [www.fairchildsemi.com](http://www.fairchildsemi.com)



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE DOES NOT COMPLY TO ANY CURRENT PACKAGING STANDARD
  - B) ALL DIMENSIONS ARE IN MILLIMETERS
  - C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS
  - D) ( ) IS REFERENCE
  - E) [ ] IS ASS'Y QUALITY
  - F) DRAWING FILENAME: MOD26ACREV3

#### LAND PATTERN RECOMMENDATIONS





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